

Silicon Controlled Rectifiers

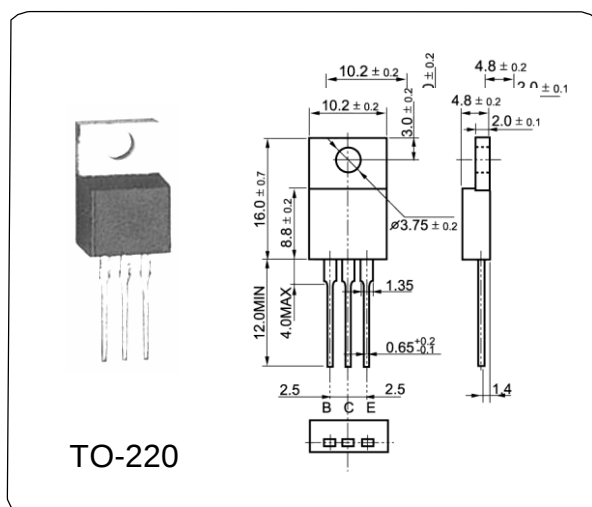
2N6509

Reverse Blocking Thyristors

- Designed primarily for half-wave ac control applications, such as motor controls, heating controls and power supply crowbar circuits.
- Glass Passivated Junctions with Center Gate Fire for Greater Parameter Uniformity and Stability
- Small, Rugged, Thermowatt Constructed for Low Thermal Resistance, High Heat Dissipation and Durability
- Blocking Voltage to 800 Volts

ABSOLUTE MAXIMUM RATINGS (Ta = 25 °C)

Parameter	Symbol	Typ	Unit
Repetitive peak off-state voltages	V_{DRM} V_{RRM}	800	V
Average on-state current	$I_{T(AV)}$	16	A
RMS on-state current	$I_{T(RMS)}$	25	A
Non-repetitive peak on-state current	I_{TSM}	250	A
Max. Operating Junction Temperature	T_j	110	°C
Storage Temperature	T_{stg}	-45~150	°C



ELECTRICAL CHARACTERISTICS (Ta = 25 °C)

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Repetitive peak off-state voltages	V_{DRM} V_{RRM}	Peak Repetitive Off—State Voltage	—	800	—	V
Average on-state current	$I_{T(AV)}$	half sine wave; $T_{mb} < 103\text{ °C}$	—	16	—	A
RMS on-state current	$I_{T(RMS)}$	all conduction angles	—	25	—	A
On-state voltage	V_T	$I_T = 50\text{ A}$	—	—	1.8	V
Holding current	I_H	$V_D = 12\text{ V}; I_{GT} = 0.1\text{ A}$	—	—	40	mA
Latching current	I_L	$V_D = 12\text{ V}; I_{GT} = 0.1\text{ A}$	—	—	45	mA
Gate trigger current	I_{GT}	$V_D = 12\text{ V}; I_T = 0.1\text{ A}$	—	9.0	30	mA
Gate trigger voltage	V_{GT}	$V_D = 12\text{ V}; I_T = 0.1\text{ A}$	—	0.6	1.5	V



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